

BF 680

SILICON PLANAR PNP

PRELIMINARY DATA

UHF MIXER-OSCILLATOR

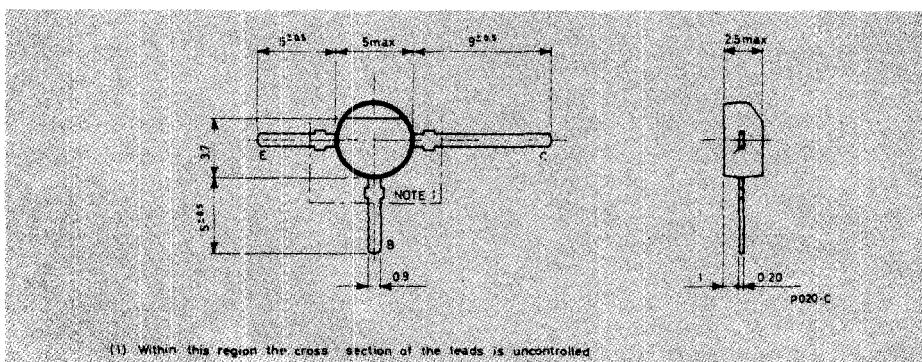
The BF 680 is a PNP silicon planar epitaxial transistor in T-plastic package. It is intended for use in TV varicap tuners as mixer-oscillator stage up to 900 MHz.

ABSOLUTE MAXIMUM RATINGS

V_{CBO}	Collector-base voltage ($I_E = 0$)	-40	V
V_{CEO}	Collector-emitter voltage ($I_B = 0$)	-35	V
V_{EBO}	Emitter-base voltage ($I_C = 0$)	-3	V
I_C	Collector current	-30	mA
I_B	Base current	-5	mA
P_{tot}	Total power dissipation at $T_{amb} \leq 45^\circ\text{C}$	170	mW
T_{stg}	Storage temperature	-55 to 150	$^\circ\text{C}$
T_j	Junction temperature	150	$^\circ\text{C}$

MECHANICAL DATA

Dimensions in mm



BF 680

THERMAL DATA

$R_{th \ j\text{-amb}}$	Thermal resistance junction-ambient	max	600	$^{\circ}\text{C/W}$
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ELECTRICAL CHARACTERISTICS ($T_{\text{amb}} = 25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{CBO} Collector cutoff current ($I_E = 0$)	$V_{\text{CB}} = -20 \text{ V}$			-100	nA
$V_{(\text{BR}) \text{ CBO}}$ Collector-base breakdown voltage ($I_E = 0$)	$I_C = -100 \mu\text{A}$		-40		V
$V_{(\text{BR}) \text{ CEO}}$ Collector-emitter breakdown voltage ($I_B = 0$)	$I_C = -5 \text{ mA}$		-35		V
$V_{(\text{BR}) \text{ EBO}}$ Emitter-base breakdown voltage ($I_C = 0$)	$I_E = -10 \mu\text{A}$		-3		V
h_{FE} DC current gain	$I_C = -3 \text{ mA} \quad V_{\text{CE}} = -10 \text{ V}$	35	50		—
f_T Transition frequency	$I_C = -3 \text{ mA} \quad V_{\text{CE}} = -10 \text{ V}$ $f = 100 \text{ MHz}$		650		MHz
C_{CBO} Collector-base capacitance	$I_E = 0 \quad V_{\text{CB}} = -10 \text{ V}$ $f = 100 \text{ MHz}$		0.6		pF
C_{rb} Reverse capacitance	$I_C = 0 \quad V_{\text{CB}} = -10 \text{ V}$ $f = 100 \text{ MHz}$		0.07		pF
NF^* Noise figure	$I_C = -3 \text{ mA} \quad V_{\text{CB}} = -10 \text{ V}$ $R_g = 50 \Omega$ $f = 800 \text{ MHz}$		5.5		dB
G_{pb}^* Power gain	$I_C = -3 \text{ mA} \quad V_{\text{CB}} = -10 \text{ V}$ $R_L = 2 \text{ k}\Omega$ $f = 800 \text{ MHz}$	11	14		dB

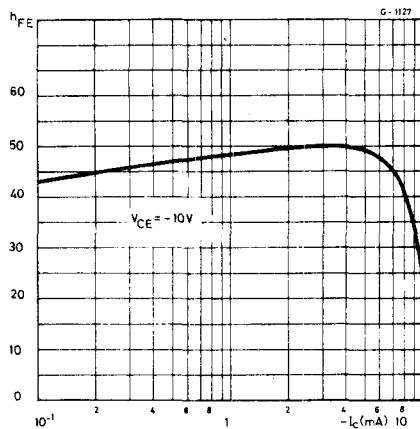
* See TEST CIRCUIT

ELECTRICAL CHARACTERISTICS (continued)

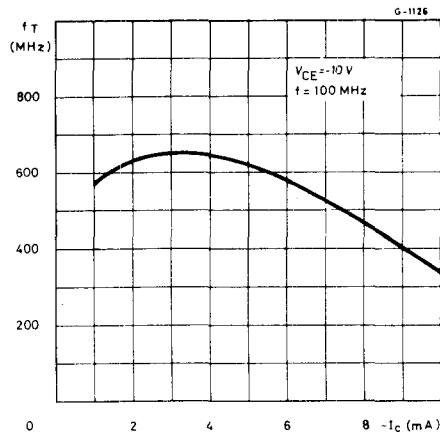
Parameter	Test conditions	Min.	Typ.	Max.	Unit
g_{ib} Input conductance	$I_C = -2 \text{ mA}$ $V_{CE} = -10 \text{ V}$ $f = 860 \text{ MHz}$ $f = 500 \text{ MHz}$		7 14		μs μs
$-b_{ib}$ Input susceptance	$I_C = -2 \text{ mA}$ $V_{CE} = -10 \text{ V}$ $f = 860 \text{ MHz}$ $f = 500 \text{ MHz}$		19 24		μs μs
$ y_{fb} $ Forward transadmittance	$I_C = -2 \text{ mA}$ $V_{CE} = -10 \text{ V}$ $f = 860 \text{ MHz}$ $f = 500 \text{ MHz}$		25 42		μs μs
ϕ_{fb} Phase angle of the forward transadmittance	$I_C = -2 \text{ mA}$ $V_{CE} = -10 \text{ V}$ $f = 860 \text{ MHz}$ $f = 500 \text{ MHz}$		50° 110°		— —
g_{ob} Output conductance	$I_C = -2 \text{ mA}$ $V_{CE} = -10 \text{ V}$ $f = 860 \text{ MHz}$ $f = 500 \text{ MHz}$		0.8 0.4		μs μs
b_{ob} Output susceptance	$I_C = -2 \text{ mA}$ $V_{CE} = -10 \text{ V}$ $f = 860 \text{ MHz}$ $f = 500 \text{ MHz}$		2.5 1.6		μs μs

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Typical DC current gain

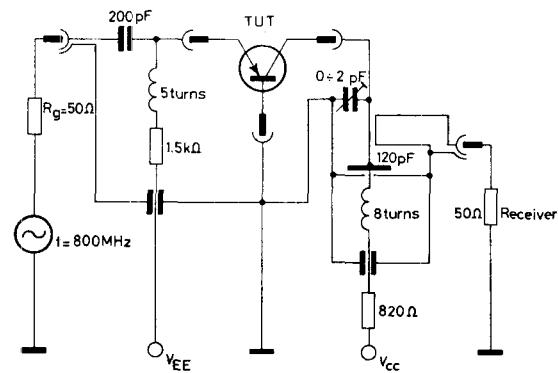


Typical transition frequency



TEST CIRCUIT

Power gain and noise figure



S-0486/1